Dual General Purpose Transistor

The NST3904DXV6T1 device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-563 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 100-300
- Low $V_{CE(sat)}$, $\leq 0.4 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- AEC-Q101 Qualified and PPAP Capable NSVT3904DXV6T1, SNST3904DXV6T5
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices

MAXIMUM RATINGS

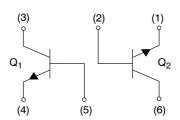
Rating		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CEO}	40	Vdc
Collector - Base Voltage		V_{CBO}	60	Vdc
Emitter - Base Voltage		V _{EBO}	6.0	Vdc
Collector Current - Continuous		Ic	200	mAdc
Electrostatic Discharge	HBM MM	ESD	>16000 >2000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com



NST3904DXV6T1

MARKING DIAGRAM



SOT-563 CASE 463A PLASTIC



MA = Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3904DXV6T1	SOT-563*	4000/Tape & Reel
NST3904DXV6T1G	SOT-563*	4000/Tape & Reel
NSVT3904DXV6T1G	SOT-563*	4000/Tape & Reel
NST3904DXV6T5	SOT-563*	8000/Tape & Reel
NST3904DXV6T5G	SOT-563*	8000/Tape & Reel
SNST3904DXV6T5G	SOT-563*	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	357 2.9	mW mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	500 4.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	250	°C/W
Junction and Storage Temperature Range	T_J , T_{stg}	-55 to +150	°C

^{1.} FR-4 @ Minimum Pad

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS			•		•	
Collector - Emitter Breakdown Volta	V _{(BR)CEO}	40	_	Vdc		
Collector - Base Breakdown Voltage	e (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	_	Vdc	
Emitter – Base Breakdown Voltage	$(I_E = 10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	6.0	_	Vdc	
Base Cutoff Current (V _{CE} = 30 Vdc	V _{EB} = 3.0 Vdc)	I _{BL}	-	50	nAdc	
Collector Cutoff Current (V _{CE} = 30)	Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	_	50	nAdc	
ON CHARACTERISTICS (Note 2)			•			
$\begin{array}{l} \text{DC Current Gain} \\ \text{(I}_{C} = 0.1 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 1.0 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 10 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 50 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \\ \text{(I}_{C} = 100 \text{ mAdc, V}_{CE} = 1.0 \text{ Vdc)} \end{array}$	h _{FE}	40 70 100 60 30	- 300 - -	-		
	V _{CE(sat)}	_ _	0.2 0.3	Vdc		
Base – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{BE(sat)}	0.65	0.85 0.95	Vdc		
SMALL-SIGNAL CHARACTERIST	rics	•	•		•	
Current - Gain - Bandwidth Produc	t (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	_	MHz	
Output Capacitance (V _{CB} = 5.0 Vdc	c, I _E = 0, f = 1.0 MHz)	C _{obo}	_	4.0	pF	
Input Capacitance (V _{EB} = 0.5 Vdc,	I _C = 0, f = 1.0 MHz)	C _{ibo}	-	8.0	pF	
Input Impedance (V _{CE} = 10 Vdc, I _C	h _{ie}	1.0 2.0	10 12	kΩ		
Voltage Feedback Ratio (V _{CE} = 10	h _{re}	0.5 0.1	8.0 10	X 10 ⁻⁴		
Small – Signal Current Gain (V _{CE} =	h _{fe}	100 100	400 400	-		
Output Admittance (V _{CE} = 10 Vdc,	h _{oe}	1.0 3.0	40 60	μmhos		
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}$, $I_{C} = 1$	NF	_ _	5.0 4.0	dB		
SWITCHING CHARACTERISTICS			1	1	1	
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc)	t _d	-	35		
Rise Time	(I _C = 10 mAdc, I _{B1} = 1.0 mAdc)	t _r	-	35	ns	
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10 mAdc)	I _C = 10 mAdc) t _s - 200		200		
Fall Time	$(I_{B1} = I_{B2} = 1.0 \text{ mAdc})$ t_f -				ns	

^{2.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.

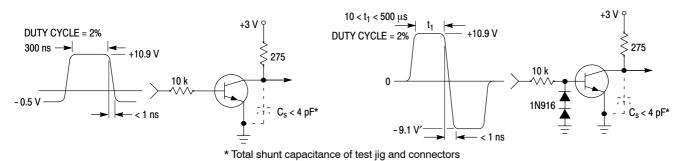


Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

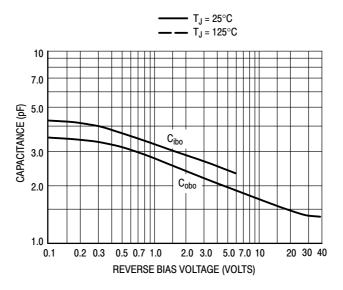
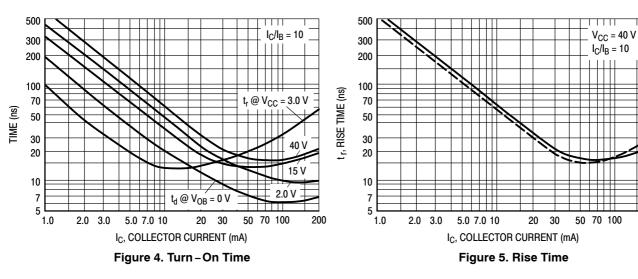


Figure 3. Capacitance



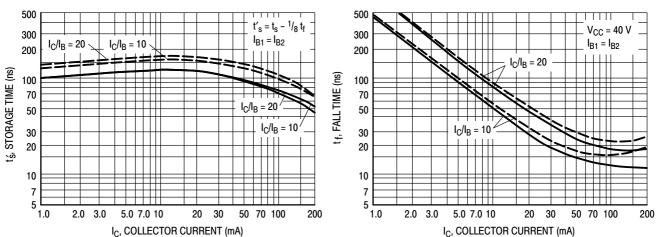


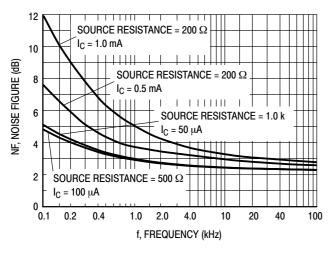
Figure 6. Storage Time

Figure 7. Fall Time

200

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



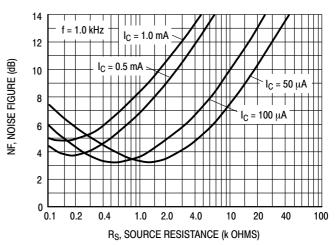


Figure 8. Noise Figure

Figure 9. Noise Figure

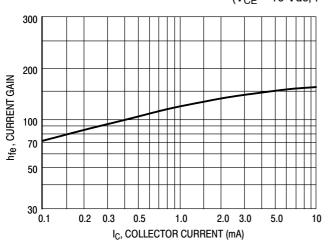
h PARAMETERS

(V_{CE} = 10 Vdc, f = 1.0 kHz, T_A = 25°C)

10

0.5

0.1



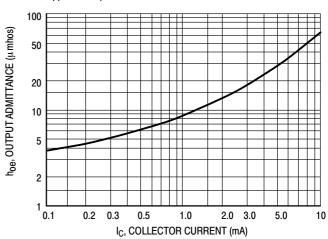


Figure 10. Current Gain

7.0 5.0 3.0 2.0 1.0 0.7

Figure 11. Output Admittance

Figure 12. Input Impedance

Figure 13. Voltage Feedback Ratio

IC, COLLECTOR CURRENT (mA)

10

, VOLTAGE FEEDBACK RATIO (x 10 -4)

TYPICAL STATIC CHARACTERISTICS

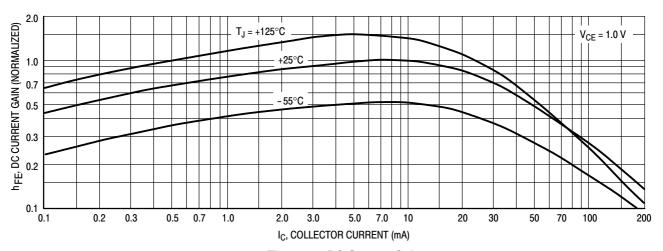


Figure 14. DC Current Gain

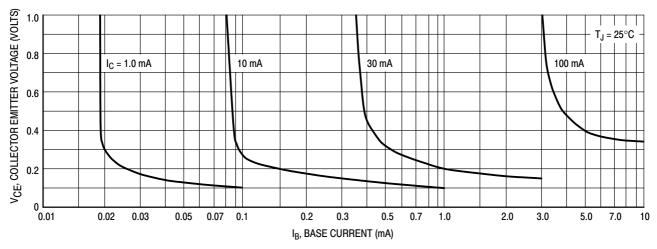


Figure 15. Collector Saturation Region

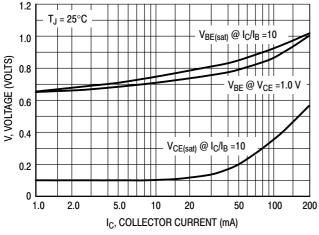


Figure 16. "ON" Voltages

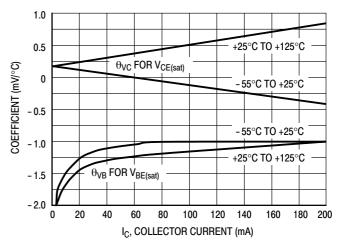
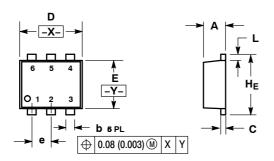


Figure 17. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01 ISSUE F

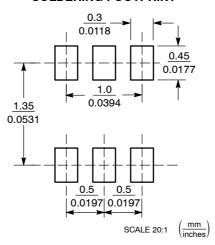


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
E	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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